

## Silicon PIN Photodiode

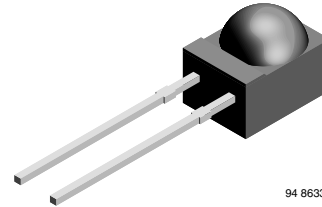
### Description

BPV23NF(L) is a high speed and high sensitive PIN photodiode in a plastic package with a spherical side view lens.

The epoxy package itself is an IR filter, spectrally matched to GaAs on GaAs and GaAlAs on GaAlAs IR emitters ( $\lambda_p = 950 \text{ nm}$ ,  $s_{rel}(\lambda = 875 \text{ nm}) > 90 \%$ ).

Lens radius and chip position are perfectly matched to the chip size, giving high sensitivity without compromising the viewing angle.

In comparison with flat packages the spherical lens package achieves a sensitivity improvement of 80 %.



### Features

- Large radiant sensitive area ( $A = 5.7 \text{ mm}^2$ )
- Wide viewing angle  $\varphi = \pm 60^\circ$
- Improved sensitivity
- Fast response times
- Low junction capacitance
- Plastic package with universal IR filter
- Option "L": long lead package optional available with suffix "L"; e.g.: BPV23FL
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



### Applications

Infrared remote control and free air transmission systems in combination with IR emitter diodes (TSU-, TSI-, or TSH.-Series). High sensitivity detector for high data rate transmission systems.

The IR filter matches perfectly to the high speed infrared emitters in the 830 nm to 880 nm wavelength range.

### Absolute Maximum Ratings

$T_{amb} = 25^\circ\text{C}$ , unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Reverse Voltage		$V_R$	60	V
Power Dissipation	$T_{amb} \leq 25^\circ\text{C}$	$P_V$	215	mW
Junction Temperature		$T_j$	100	$^\circ\text{C}$
Operating Temperature Range		$T_{amb}$	- 55 to + 100	$^\circ\text{C}$
Storage Temperature Range		$T_{stg}$	- 55 to + 100	$^\circ\text{C}$
Soldering Temperature	$t \leq 5 \text{ s}$	$T_{sd}$	260	$^\circ\text{C}$
Thermal Resistance Junction/Ambient		$R_{thJA}$	350	K/W

## Electrical Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Forward Voltage	$I_F = 50\text{ mA}$	$V_F$		1	1.3	V
Breakdown Voltage	$I_R = 100\text{ }\mu\text{A}$ , $E = 0$	$V_{(BR)}$	60			V
Reverse Dark Current	$V_R = 10\text{ V}$ , $E = 0$	$I_{ro}$		2	30	nA
Diode capacitance	$V_R = 0\text{ V}$ , $f = 1\text{ MHz}$ , $E = 0$	$C_D$		48		pF
Serial Resistance	$V_R = 12\text{ V}$ , $f = 1\text{ MHz}$	$R_S$		900		$\Omega$

## Optical Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Open Circuit Voltage	$E_e = 1\text{ mW/cm}^2$ , $\lambda = 950\text{ nm}$	$V_o$		390		mV
Temp. Coefficient of $V_o$	$E_e = 1\text{ mW/cm}^2$ , $\lambda = 950\text{ nm}$	$TK_{V_o}$		- 2.6		mV/K
Short Circuit Current	$E_e = 1\text{ mW/cm}^2$ , $\lambda = 950\text{ nm}$	$I_k$		65		$\mu\text{A}$
Reverse Light Current	$E_e = 1\text{ mW/cm}^2$ , $\lambda = 870\text{ nm}$ , $V_R = 5\text{ V}$	$I_{ra}$	45	65		$\mu\text{A}$
Temp. Coefficient of $I_{ra}$	$E_e = 1\text{ mW/cm}^2$ , $\lambda = 950\text{ nm}$ , $V_R = 10\text{ V}$	$TK_{I_{ra}}$		0.1		%/K
Absolute Spectral Sensitivity	$V_R = 5\text{ V}$ , $\lambda = 870\text{ nm}$	$s(\lambda)$		0.57		A/W
	$V_R = 5\text{ V}$ , $\lambda = 950\text{ nm}$	$s(\lambda)$		0.60		A/W
Angle of Half Sensitivity		$\phi$		$\pm 60$		deg
Wavelength of Peak Sensitivity		$\lambda_p$		940		nm
Range of Spectral Bandwidth		$\lambda_{0.5}$		790 to 1050		nm
Quantum Efficiency	$\lambda = 950\text{ nm}$	$\eta$		90		%
Noise Equivalent Power	$V_R = 10\text{ V}$ , $\lambda = 950\text{ nm}$	NEP		$4 \times 10^{-14}$		W/ $\sqrt{\text{Hz}}$
Detectivity	$V_R = 10\text{ V}$ , $\lambda = 950\text{ nm}$	$D^*$		$5 \times 10^{12}$		$\text{cm}^2/\text{Hz/W}$
Rise Time	$V_R = 10\text{ V}$ , $R_L = 1\text{ k}\Omega$ , $\lambda = 820\text{ nm}$	$t_r$		70		ns
Fall Time	$V_R = 10\text{ V}$ , $R_L = 1\text{ k}\Omega$ , $\lambda = 820\text{ nm}$	$t_f$		70		ns
Cut-Off Frequency	$V_R = 12\text{ V}$ , $R_L = 1\text{ k}\Omega$ , $\lambda = 870\text{ nm}$	$f_c$		4		MHz
	$V_R = 12\text{ V}$ , $R_L = 1\text{ k}\Omega$ , $\lambda = 950\text{ nm}$	$f_c$		1		MHz

## Typical Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified

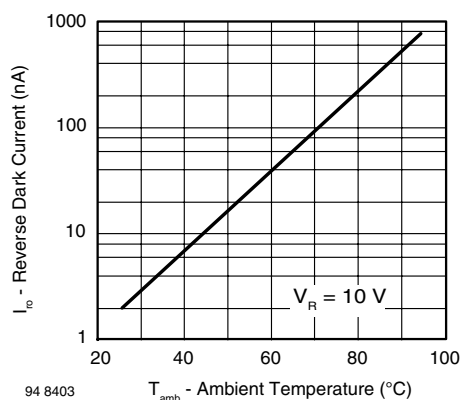


Figure 1. Reverse Dark Current vs. Ambient Temperature

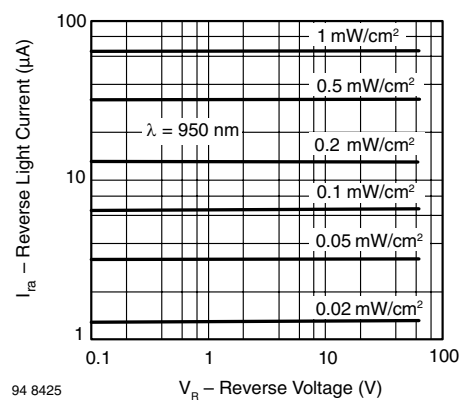


Figure 4. Reverse Light Current vs. Reverse Voltage

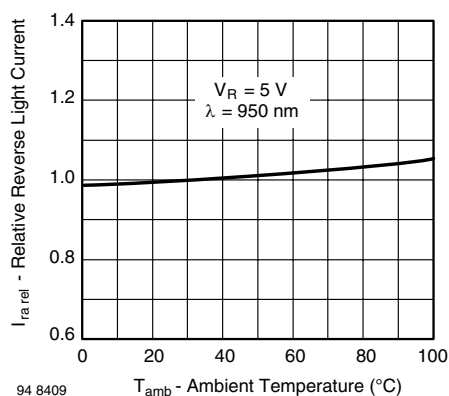


Figure 2. Relative Reverse Light Current vs. Ambient Temperature

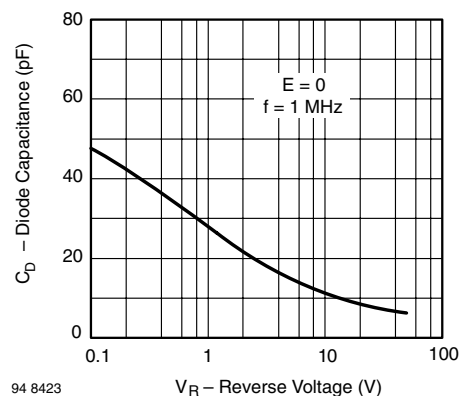


Figure 5. Diode Capacitance vs. Reverse Voltage

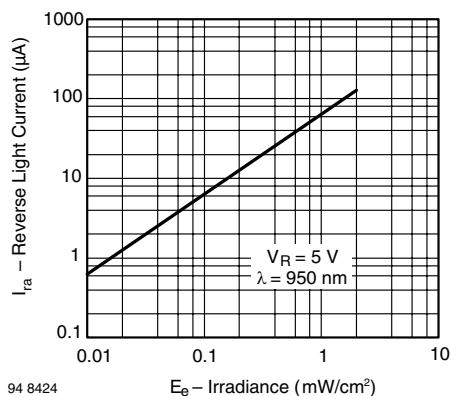


Figure 3. Reverse Light Current vs. Irradiance

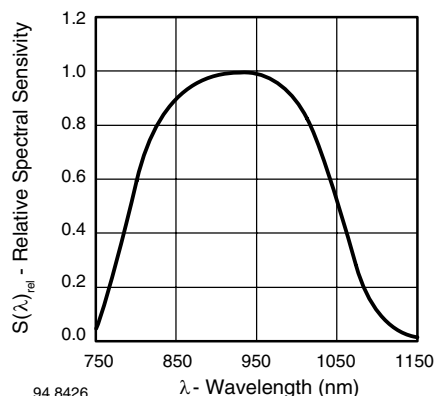
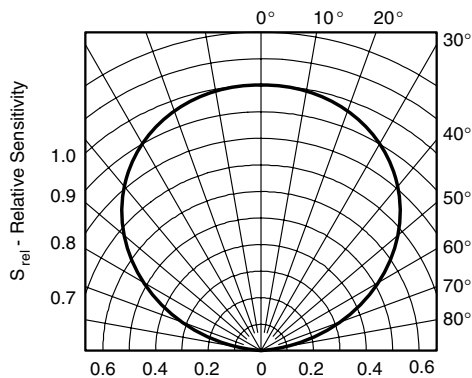


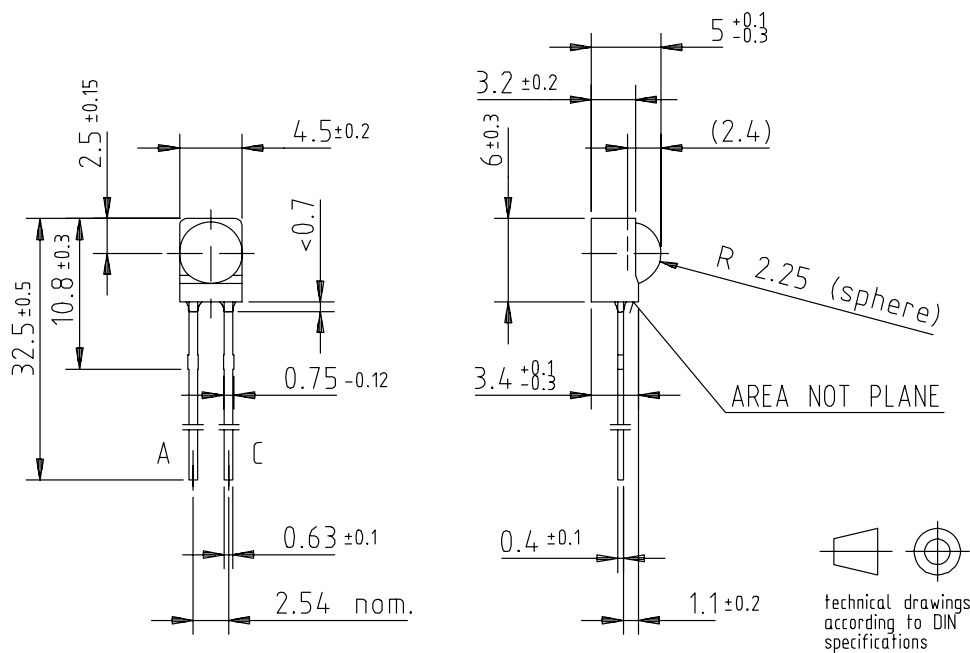
Figure 6. Relative Spectral Sensitivity vs. Wavelength



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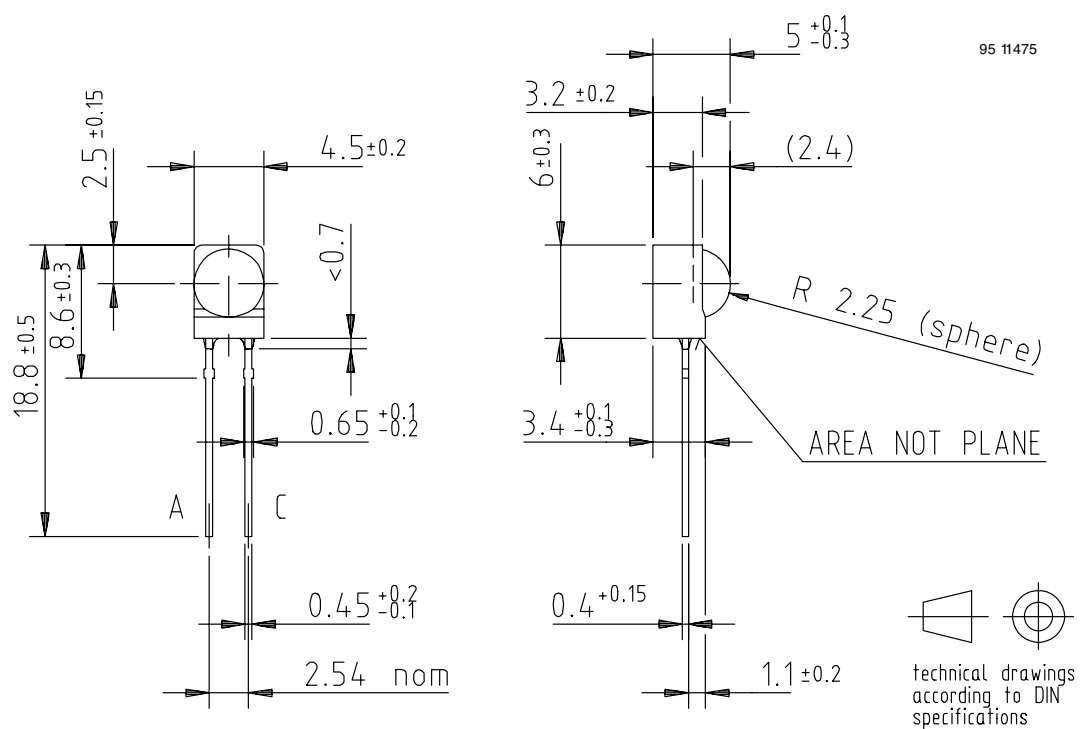
Figure 7. Relative Radiant Sensitivity vs. Angular Displacement

## Package Dimensions in mm



9612205

**Package Dimensions in mm**



## Ozone Depleting Substances Policy Statement

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1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

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